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cont. 20. A material according to claim 18, having a peel strength of 0.5 kgf/5 mm x 5 mm chip or higher at a stage where a semiconductor has been bonded to a support member with said material.

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21. A material according to claim 20, said material having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

22. A material according to claim 17, said material having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

Sub B3 > 23. A material according to claim 22, having a peel strength of 0.5 kgf/5 mm x 5 mm chip or higher at a stage where a semiconductor has been bonded to a support member with said material.

24. A material comprising an organic die-bonding film having a saturation moisture absorption of 1.0% by volume or less.

25. A material comprising an organic die-bonding film having a residual volatile component in an amount of not more than 3.0% by weight.

26. A material according to claim 24, having a residual volatile component in an amount of not more than 3.0% by weight.

27. A material comprising an organic die-bonding film having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

28. A material comprising an organic die-bonding film having a void volume of 10% or less in terms of voids present in the material and at an interface between said material and a support member at a stage where a semiconductor has been bonded to said support member.

29. A material comprising an organic die-bonding film having a peel strength of 0.5 kgf/5 mm x 5 mm chip or higher at a stage where a semiconductor has been bonded to a support member with said material.

30. A material according to claim 29, having a saturation moisture absorption of 1.0% by volume or less.

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Sub B47

31. A material according to claim 29, having a residual volatile component in an amount of not more than 3.0% by weight.

32. A material according to claim 30, having a residual volatile component in an amount of not more than 3.0% by weight.

33. A material according to claim 29, having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

34. A material according to claim 17, including at least one component selected from an epoxy resin, a silicon resin, an acryl resin and a polyimide resin.

Sub B47

35. A material according to claim 34, said component including a polyimide resin.

36. A material according to claim 34, said component including an epoxy resin, said epoxy resin being any one of glycidyl ether, glycidylamine, glycidyl ester and an alicyclic epoxy resin.

37. A material according to claim 27, including at least one component selected from an epoxy resin, a silicon resin, an acryl resin and a polyimide resin.

38. A material according to claim 37, said component including a polyimide resin.

39. A material comprising an organic die-bonding film according to claim 21, said component including an epoxy resin, said epoxy resin being any one of glycidyl ether, glycidylamine, glycidyl ester and an alicyclic epoxy resin.

Sub B5

40. A material comprising an organic die-bonding film according to claim 1, further including an inorganic filler.

41. A material comprising an organic die-bonding film according to claim 27, further including an inorganic filler.

Sub B6 42. A method of bonding a semiconductor chip to a support member wherein said material comprising an organic die-bonding film according to claim 17 is used for said bonding.

Q2 concd 43. A method of bonding according to claim 42, wherein said bonding is carried out at a temperature of 100-350°C for a time period of 0.1 second - 20 seconds with a pressure of 0.1 - 20 gf/mm².

44. A method of bonding according to claim 43, wherein said bonding is carried out at a temperature of 150 - 250°C for a time period not longer than 2 seconds, with a pressure of 4 gf/mm² or less.

45. A method of bonding according to claim 44, wherein said bonding is carried out for a time period 1.5 seconds or less, with a pressure of 0.3 - 2 gf/mm².

46. A method of bonding the support member to the semiconductor chip with a material comprising an organic die-bonding film according to claim 27.

47. A method of bonding according to claim 46, wherein said bonding is carried out at a temperature of 100 - 350°C for a time period of 0.1 second - 20 seconds with a pressure of 0.1-20 gf/mm².

48. A method of bonding according to claim 47, wherein said bonding is carried out at a temperature of 150 - 250°C for a time period of less than 2 seconds with a pressure of 4 gf/mm².

49. A method of bonding according to claim 48, wherein said bonding is carried out for a time period of 1.5 seconds or less with a pressure of 0.3-2 gf/mm².

Sub B7 50. A semiconductor device manufactured using a material comprising an organic die-bonding film according to claim 17.

51. A semiconductor device manufactured using a material comprising an organic die-bonding film according to claim 27.